

THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

PEATMAN, WILLIAM C., et al.

Application No.: 09/592349

Filed: 6/12/2000

Docket No.: SC11100ZP

§ Patent No.: 6821829

§ Issue Date: 11/23/2004

§ Examiner: Douglass Wille

§ Group Art Unit: 2814

Title: METHOD OF MANUFACTURING A SEMICONDUCTOR COMPONENT AND  
SEMICONDUCTOR COMPONENT THEREOF

Certificate of Submission

I hereby certify that this correspondence is being submitted to  
the U.S.P.T.O., Alexandria, VA.

Addressed per C.F.R. § 1.1(a) and deposited with the  
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Submitted electronically via EFS in accordance with  
"Legal Framework for EFS Web".

9/20/06

Date of Submission

Pat Thomas

Printed Name of Person Signing Certificate

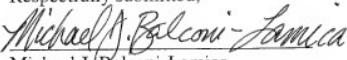
Commissioner for Patents  
Alexandria, VA 22313

SUBMISSION OF CERTIFICATE OF CORRECTION

Dear Commissioner:

Enclosed is a Certificate of Correction listing error(s) in the subject patent. Please enter  
these corrections which were made in an Examiner's amendment. Since the errors appear to be  
on the part of the United States Patent Office, there should be no charge.

Respectfully submitted,



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9/20/06  
Date

**UNITED STATES PATENT AND TRADEMARK OFFICE**  
**CERTIFICATE OF CORRECTION**

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PATENT NO.: 6821829  
APPLICATION NO: 09/592349  
DATE: 11/23/2004  
INVENTOR(S): PEATMAN, WILLIAM C.

It is certified that error appears in the above-identified patent and that said Letters Patent are hereby corrected as shown below:

In Column 8, After Line 36, Claim No. 11:

Insert "forming a dielectric layer over the gate contact, the remaining first portion of the undoped gallium arsenide capping layer and the exposed portion of the surface of the delta-doped heteroepitaxial semiconductor substrate;"

MAILING ADDRESS OF SENDER (Please do not use customer number below)

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Austin, TX 78729